

Future Packaging Technologies in Power Electronic Modules

@Fraunhofer IISB



Content

Part One

Some Words on Fraunhofer Institutes
- from the general to the specific -

Part Two

Future Packaging Technologies in Power
Electronic Modules

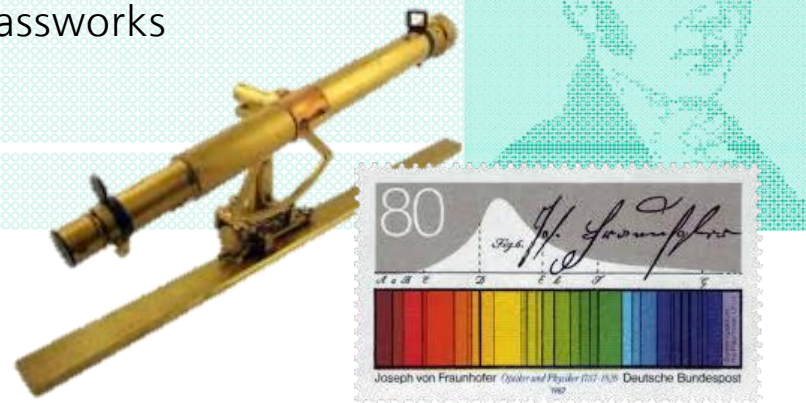
JOSEPH VON FRAUNHOFER

(1787 – 1826)

The **Fraunhofer-Gesellschaft** is a recognized non-profit organization that takes its name from '**Joseph von Fraunhofer**' (1787–1826), the illustrious Munich researcher, inventor and entrepreneur.

- **Researcher** – discovery of the 'Fraunhofer lines' in the solar spectrum
- **Inventor** – new processing method for lenses
- **Entrepreneur** – director and partner in a glassworks

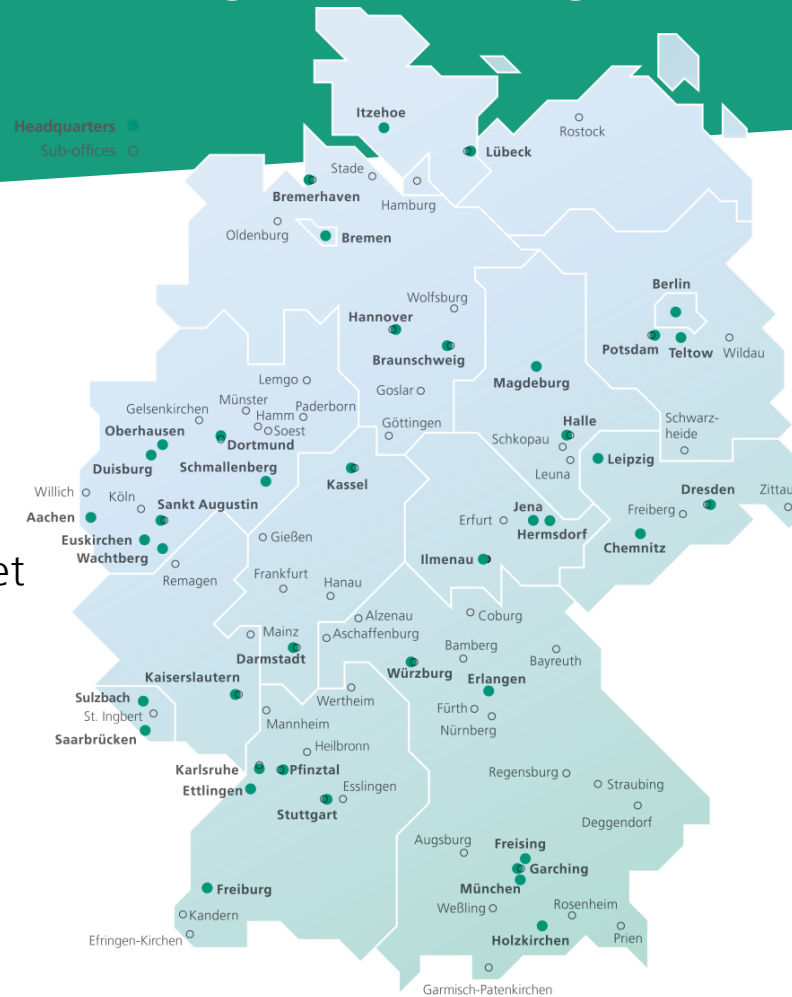
- **Fraunhofer foundation in 1949**
→ from military to recent industrial research and engineering (today's staff 24,500)



INSTITUTES AND RESEARCH ESTABLISHMENTS IN GERMANY

Fraunhofer Research Institutes

- Legal status: Non-profit association (e.V.)
- Mission: Application-oriented R&D
- 72 institutes with approx. 2.1 billion euros budget
- Through contract research 1.9 billion euros
- About 70 pct. of the Fraunhofer-Gesellschaft's contract research revenue comes from publicly financed research projects



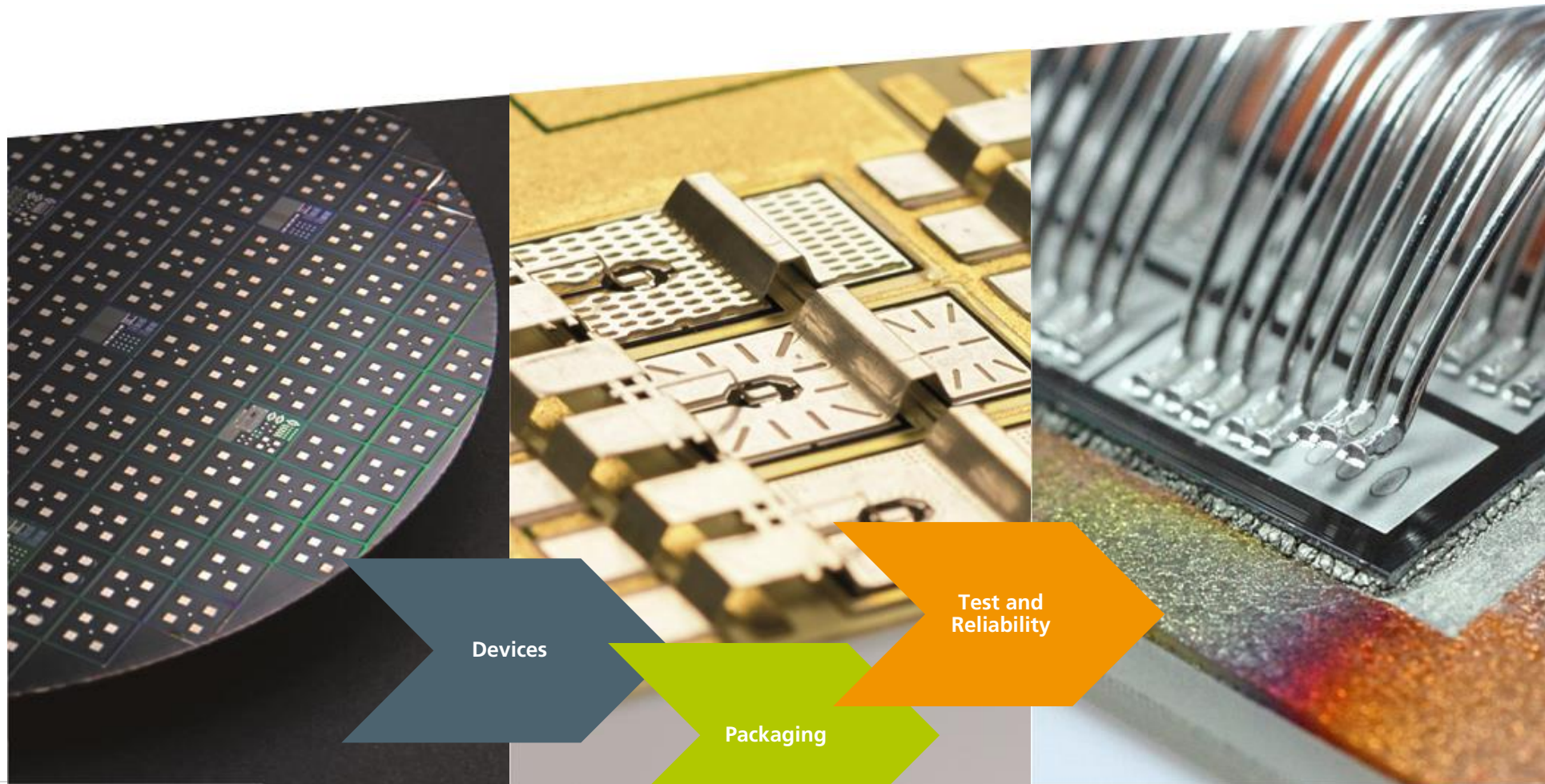
POWER ELECTRONIC SYSTEMS

From Material to Power Electronic Applications



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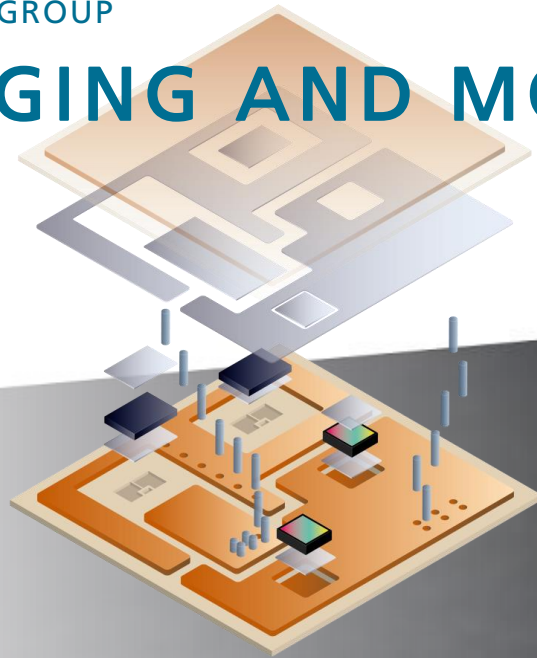
DEVICES AND RELIABILITY



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DEPARTMENT → GROUP

PACKAGING AND MODULES



New Concepts and Materials for Packaging

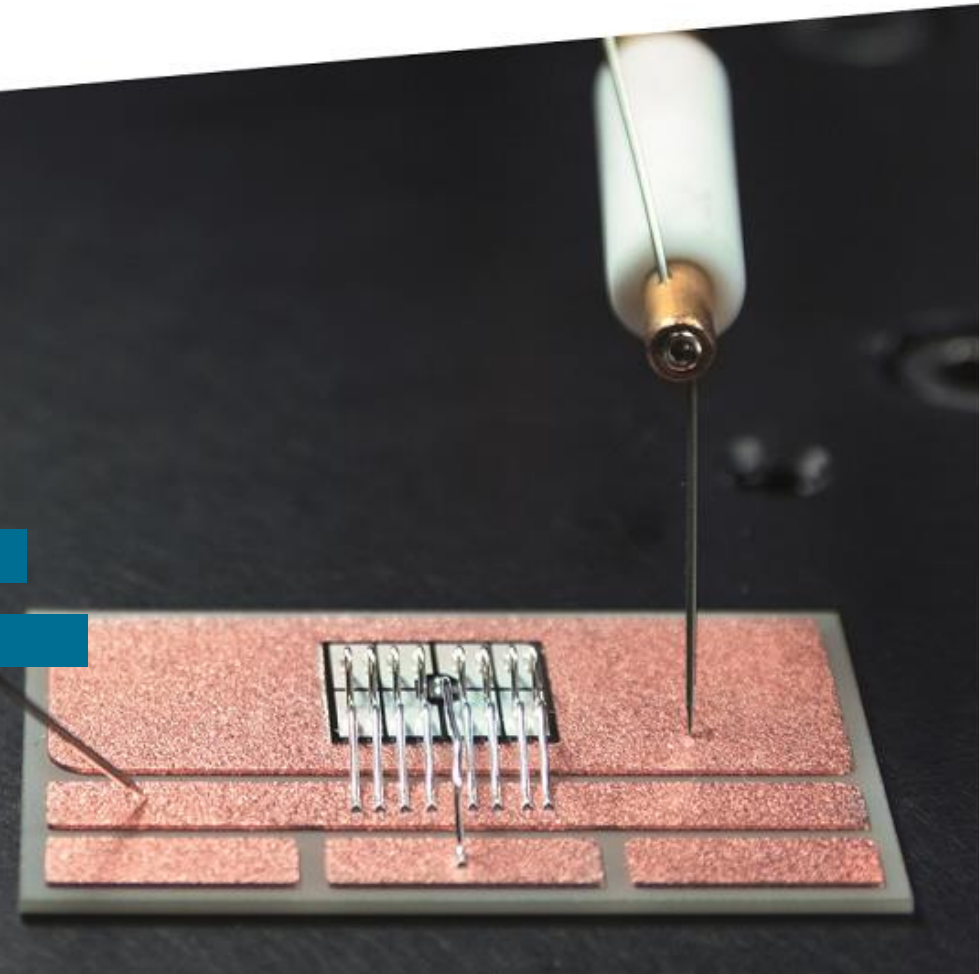
High Performance Joining Technologies, Sintering

Thermal, Electrical, and Mechanical Characterization

Lifetime Characterization, Statistical Analysis

Analysis of Failure Mechanism

Lifetime Modeling



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Future Packaging Technologies in Power Electronic Modules

- New Connection Technologies for Recent Modules
 - Si Modules with IISB Addon for SiC
 - Double Sided Sintering
 - Spot Welding for Terminals
- Sintering → Selective Sintering on Organic Substrates
- Die-to-Die Bonding for Power Electronics
- Ceramic Embedding
 - Diamond Devices and WBG in Hot Hermetic Housings
- Outlook in Further Projects
 - Simulation in Power Electronics and Topology Optimization
 - Lifetime, Corrosion and Environmental Issues

New Connection Technologies for Recent Modules

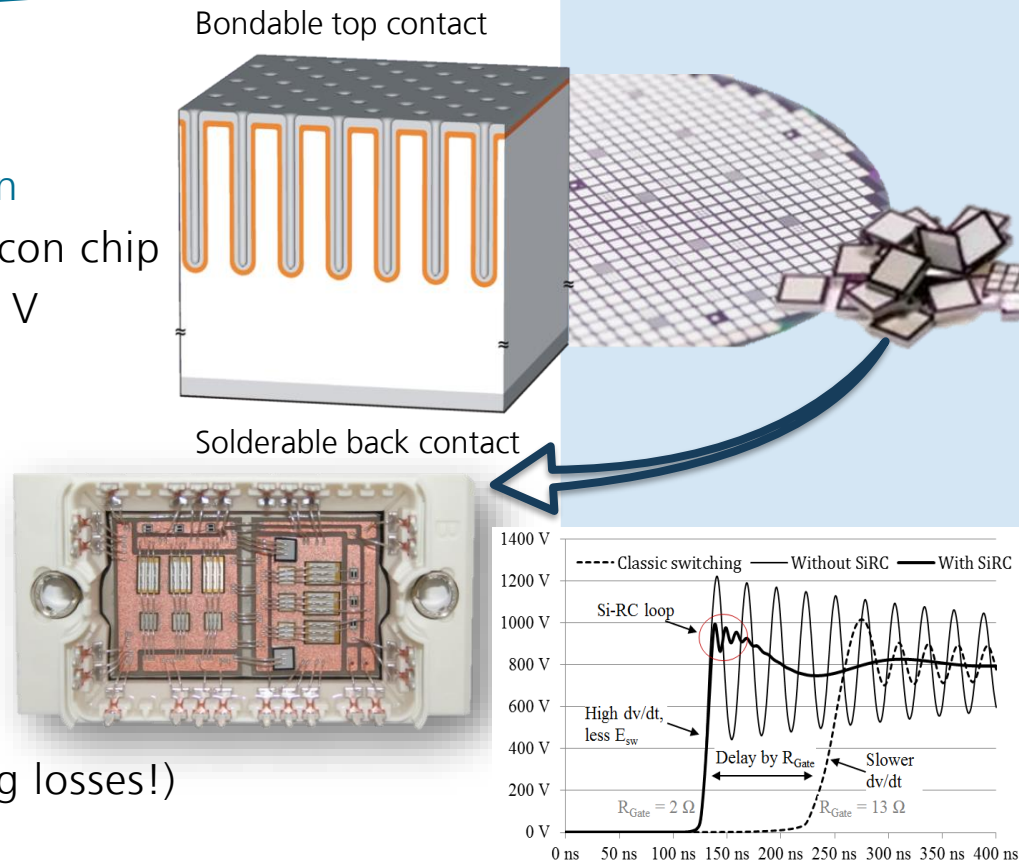
Si Modules with IISB Addon for SiC¹⁻⁵

Device Concept and Implementation

- RC-snubber combination on a silicon chip
- Voltage rating: e.g. 200 V to 900 V
- Capacitance: typ. 5 nF to 30 nF

Comparison of Switching Methods

- Classic slow (200 V overshoot)
- High speed (400 V overshoot, -50 % switching losses)
- High speed with Snubber (200 V overshoot, -50% switching losses!)



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New Connection Technologies for Recent Modules

Double Sided Sintering⁶⁻¹⁰

Sintering of Both Sides of the Devices

1. Top side leadframe
 - Pressure-assisted device sintering
 - Pressure-assisted or -less leadframe sintering



2. Top side DBC/DBA/AMB



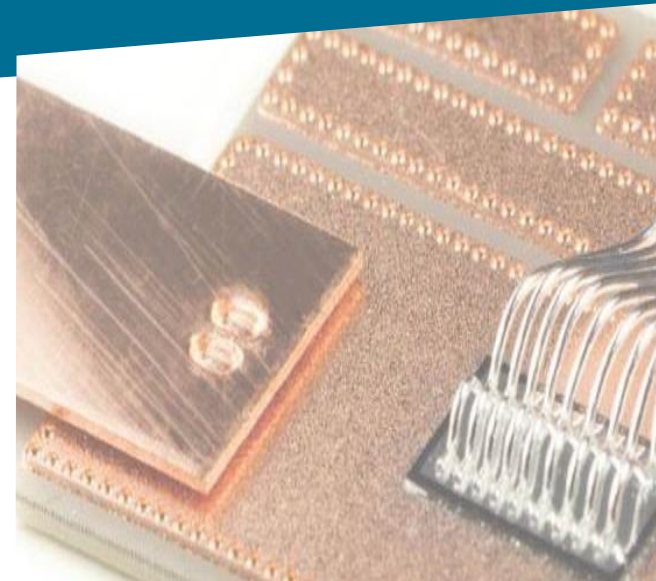
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New Connection Technologies for Recent Modules

Spot Welding for Terminals¹¹

Spot Welding of Copper Terminals to DBC Circuit Carriers

- Cu/Cu bonding with no interconnection layer
- Low thermal and mechanical stress during process
- DBC ceramic AlN and Al₂O₃
- High lifetime and no lifetime impact on surroundings



Selective Sintering on Organic Substrates¹²⁻¹³

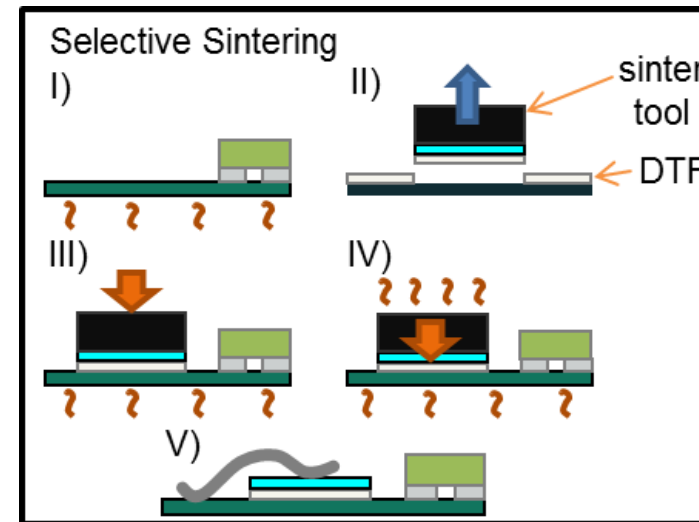


General Sintering Topics

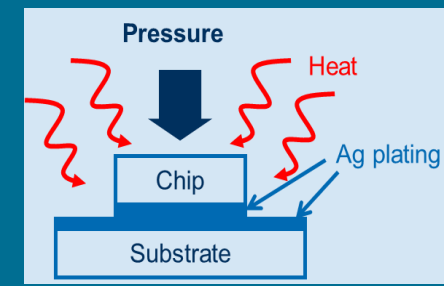
- Pressure-assisted sintering with different materials, such as silver-with-copper paste or copper paste
- Pressure-less sintering
- Jet dispensing of sinter/solder paste
- Selective sintering

Sintering of Bare Dies or SMD Devices on pre-populated Circuit Boards

- Selective sintering process
 - Picking device then sinter film (DTF), placing
 - Final sintering by die placer



Die to Die Bonding for Power Electronics¹⁴⁻¹⁵



Goal

- Bonding without explicit bonding material (without solder/sinter paste)

Solution

- Chip on chip bonding from MEMS adopted to power electronics
→ enabling technology: general sintering

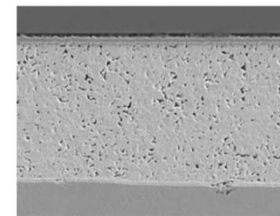
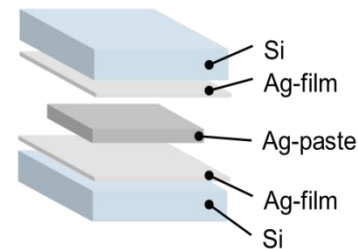
Highlights

- High integration density, high temperature capability >300 °C

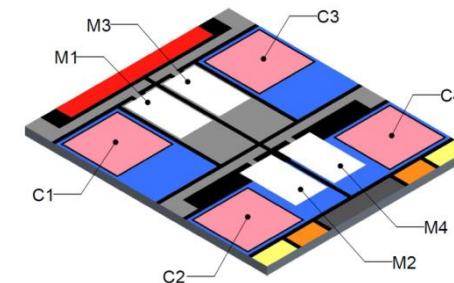
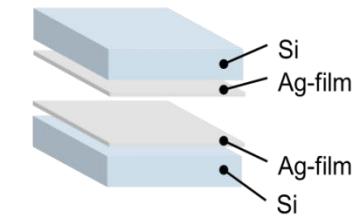
Relevance

- Heterogeneous packaging
- Research directions – bonding without bonding material
 - Chip-on-chip, chip-on-interposer, chip-on-DBC/DBA/AMB
 - Chip/device stacking → more than two dies with adaption of chip metallization and insulation

Silver sintering



Direct Ag to Ag bonding



48 V to pol-converter with GaN package

Ceramic Embedding

Diamond Devices and WBG in Hot Hermetic Housings¹⁶⁻¹⁸

Goal

- Compact and hermetic high temperature packaging for high voltage

Issue

- State of the art organic materials do not cover wide band gap (WBG) semiconductor devices' demands

Solution

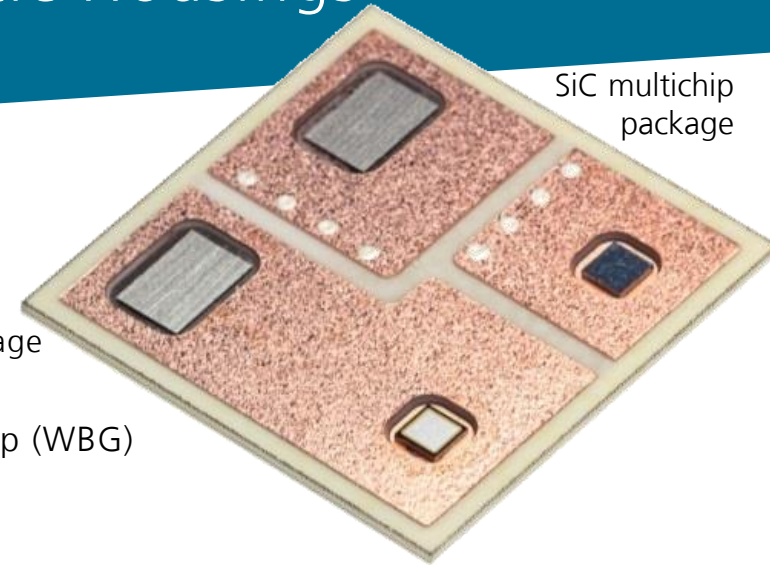
- Embedding in ceramic circuit board like DBC/DBA/AMB
- Subtractive laser ablation for extremely fine pitch and cavities

Highlights

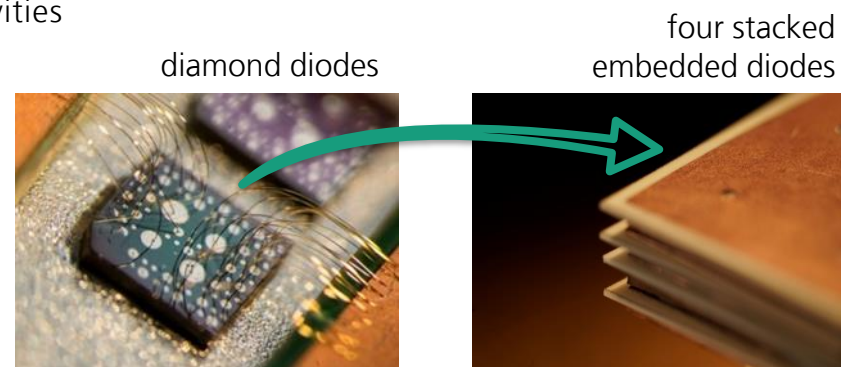
- High integration density
- High temperature capability $>300\text{ }^{\circ}\text{C}$
- High voltage resistant ($>12\text{ kV}$ demonstrated)
- Hermetic for harsh environments

Relevance

- Air cooled power electronics solutions



SiC multichip package

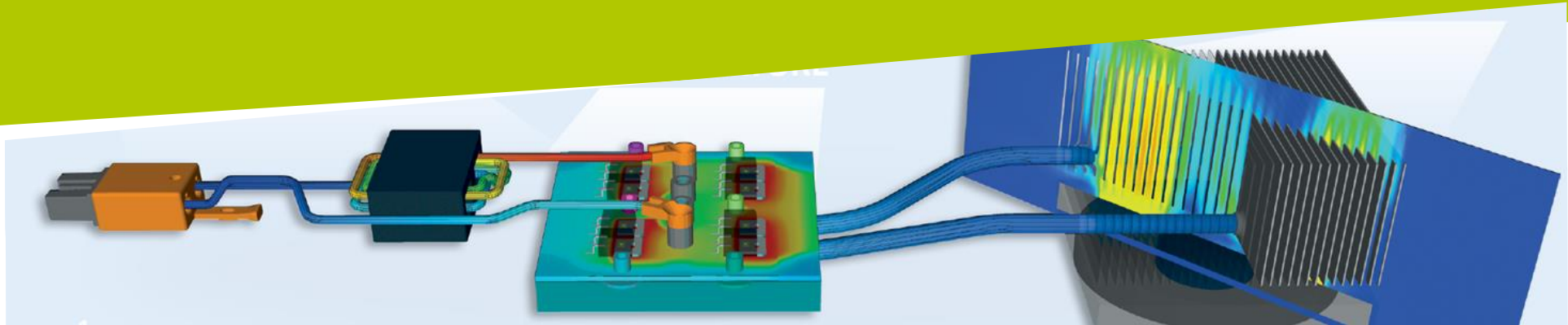


diamond diodes

four stacked embedded diodes

Outlook in Further Projects

Simulation in Power Electronics and Topology Optimization¹⁹⁻²³



Simulation – Optimization – Rapid Prototyping

- Electrical, thermal, and mechanical simulation on device, module, and system level, electronic cooling design, thermal management, as well as extraction of electric parasitics and circuit simulation
- Coupled and multiphysics simulations
→ topology optimization, automated topology generation
- Subtractive and additive prototype generation of various power electronic components
→ 3D printing at IISB (ceramic, metal, organic), laser ablation for fast DCB structures

Outlook in Further Projects

Lifetime, Corrosion and Environmental Issues²⁴⁻³⁴

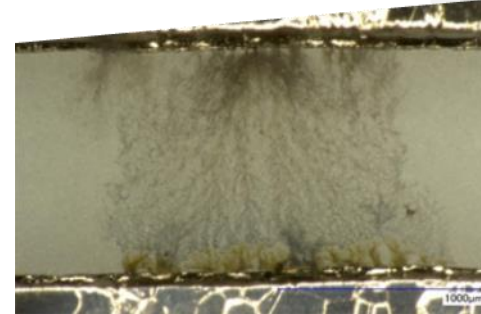
Lifetime Testing and Analysis

- Thermo-mechanical testing
 - Power cycling test, temperature cycling or shock test
- Chemical/environmental testing
 - Humidity, salt spray or corrosion gas testing
- Analysis
 - SEM, SAM, FIB (focussed ion beam), grinding, laser ablation, surface characterization techniques, lock-in thermography etc.

Lifetime Concepts and Coating

- Application of high temperature capable and narrow gap filling coating systems (e.g., Parylene)
- Conception of novel test methods for application oriented tests of insulation systems in WBG power modules
- Concepts for passives lifetime characterization and testing of capacitors

Active power cycling testing



Dendrite growth in isolation gap of a power module

Localized defect on IGBT by lock-in thermography



DEVICES AND RELIABILITY

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Addon → Corrosion Clip

Electrochemical Corrosion (ECM)

https://www.iisb.fraunhofer.de/en/research_areas/packaging_reliability.html

THANK YOU FOR YOUR ATTENTION!

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